Low Noise Transistor

NPN Silicon

Features

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	60	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	Ic	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

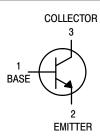
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



1U = Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT2484LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ noted)$

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·			
Collector – Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	60	_	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$)	V _(BR) CBO	60	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	-	Vdc
Collector Cutoff Current $(V_{CB} = 45 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 45 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$	I _{CBO}	- -	10 10	nAdc μAdc
Emitter Cutoff Current (V _{EB} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	10	nAdc
ON CHARACTERISTICS	<u> </u>			
DC Current Gain $ \begin{aligned} &(I_C = 1.0 \text{ mAdc, V}_{CE} = 5.0 \text{ Vdc}) \\ &(I_C = 10 \text{ mAdc, V}_{CE} = 5.0 \text{ Vdc}) \end{aligned} $	h _{FE}	250 -	_ 800	-
Collector – Emitter Saturation Voltage (I _C = 1.0 mAdc, I _B = 0.1 mAdc)	V _{CE(sat)}	-	0.35	Vdc
Base – Emitter On Voltage (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc)	V _{BE(on)}	-	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	_	6.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}, I_{C} = 0, f = 1.0 \text{ MHz}$)	C _{ibo}	-	6.0	pF
Noise Figure (I _C = 10 μ Adc, V _{CE} = 5.0 Vdc, R _S = 10 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	-	3.0	dB

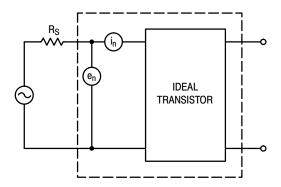
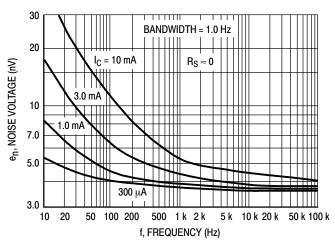


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

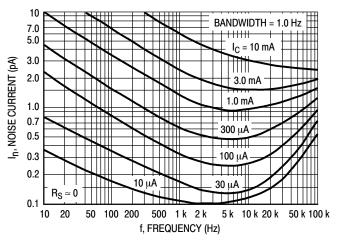
NOISE VOLTAGE



BANDWIDTH = 1.0 Hz 20 $R_S\approx 0\,$ en, NOISE VOLTAGE (nV) f = 10 Hz 10 100 Hz 7.0 1.0 kHz 5.0 3.0 0.02 0.2 0.5 1.0 0.01 0.05 0.1 5.0 10 IC, COLLECTOR CURRENT (mA)

Figure 2. Effects of Frequency

Figure 3. Effects of Collector Current



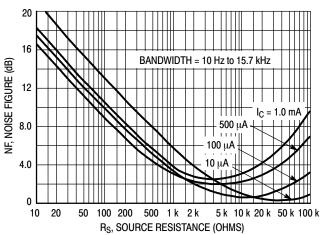
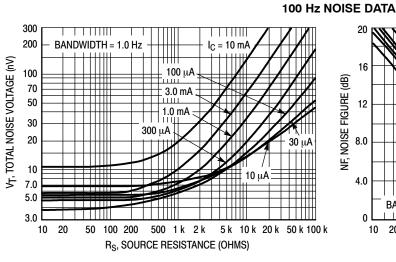


Figure 4. Noise Current

Figure 5. Wideband Noise Figure



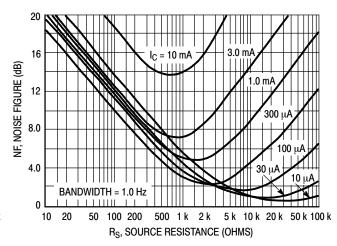


Figure 6. Total Noise Voltage

Figure 7. Noise Figure

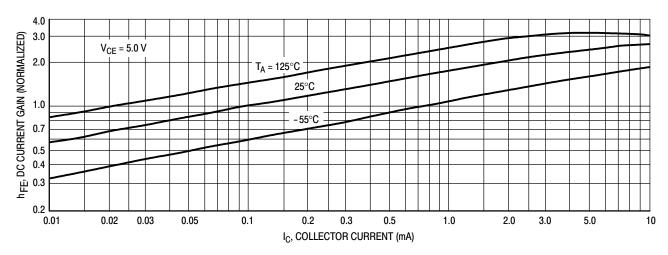


Figure 8. DC Current Gain

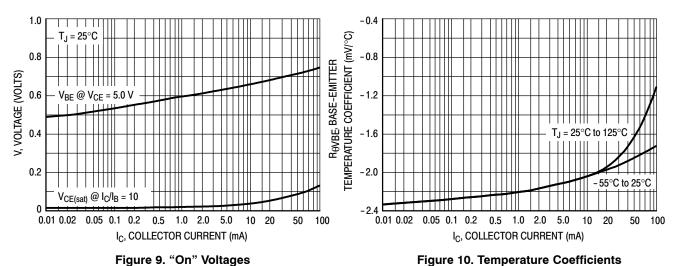


Figure 9. "On" Voltages

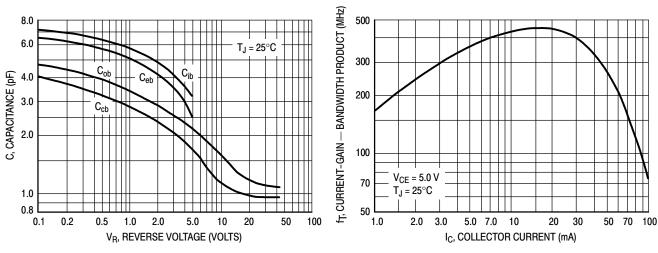
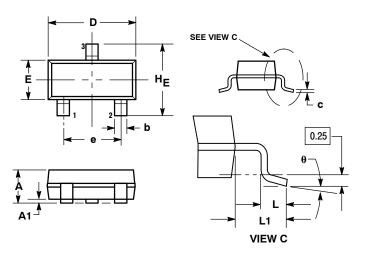


Figure 11. Capacitance

Figure 12. Current-Gain — Bandwidth Product

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



NOTES

- DIMENSIONING AND TOLERANCING PER

- ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

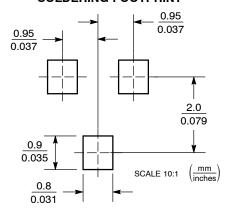
 3. MAXIMUM LEAD THICKNESS INCLUDES
 LEAD FINISH THICKNESS. MINIMUM LEAD
 THICKNESS IS THE MINIMUM THICKNESS OF
 PACE MATERIAL BASE MATERIAL.
- 4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
C	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
ө	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
He	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

- PIN 1. BASE 2. EMITTER COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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